

### Description

The DFI75FB12P3H2 offer lower losses and higher energy for application such as motor drive, inverter and soft switching applications.



### Features

- 1200V75 A,  $V_{CE(sat)}(typ.) = 1.60V$
- Lower losses and higher energy
- Excellent short-circuit capability

### Applications

- Motor drive
- Inverter
- Welding machines
- UPS

### Circuit diagram

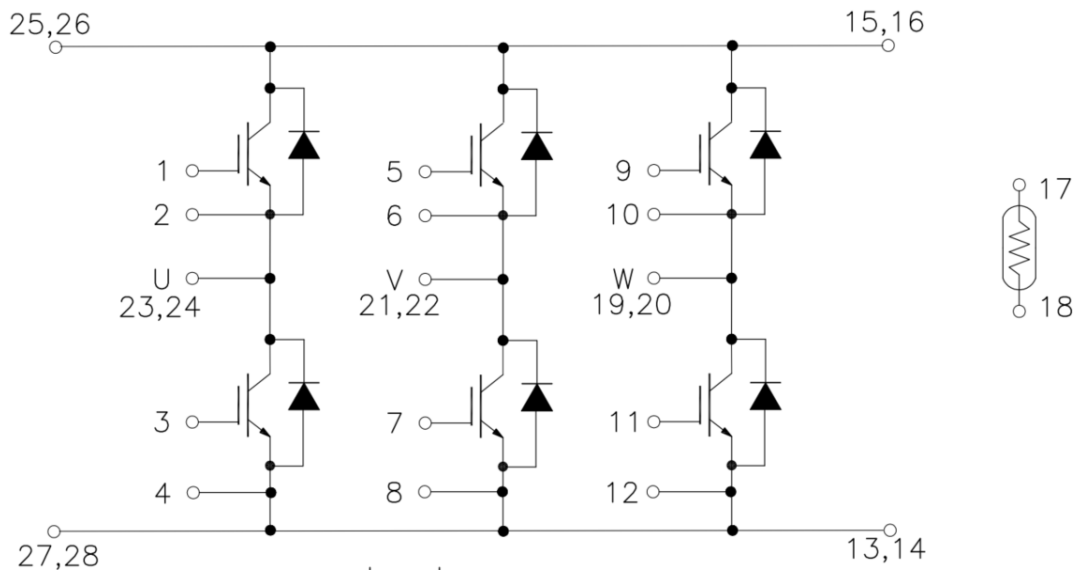


Figure 1. Out drawing & circuit diagram for DFI75FB12P3H2

### Pin Configuration and Marking Information

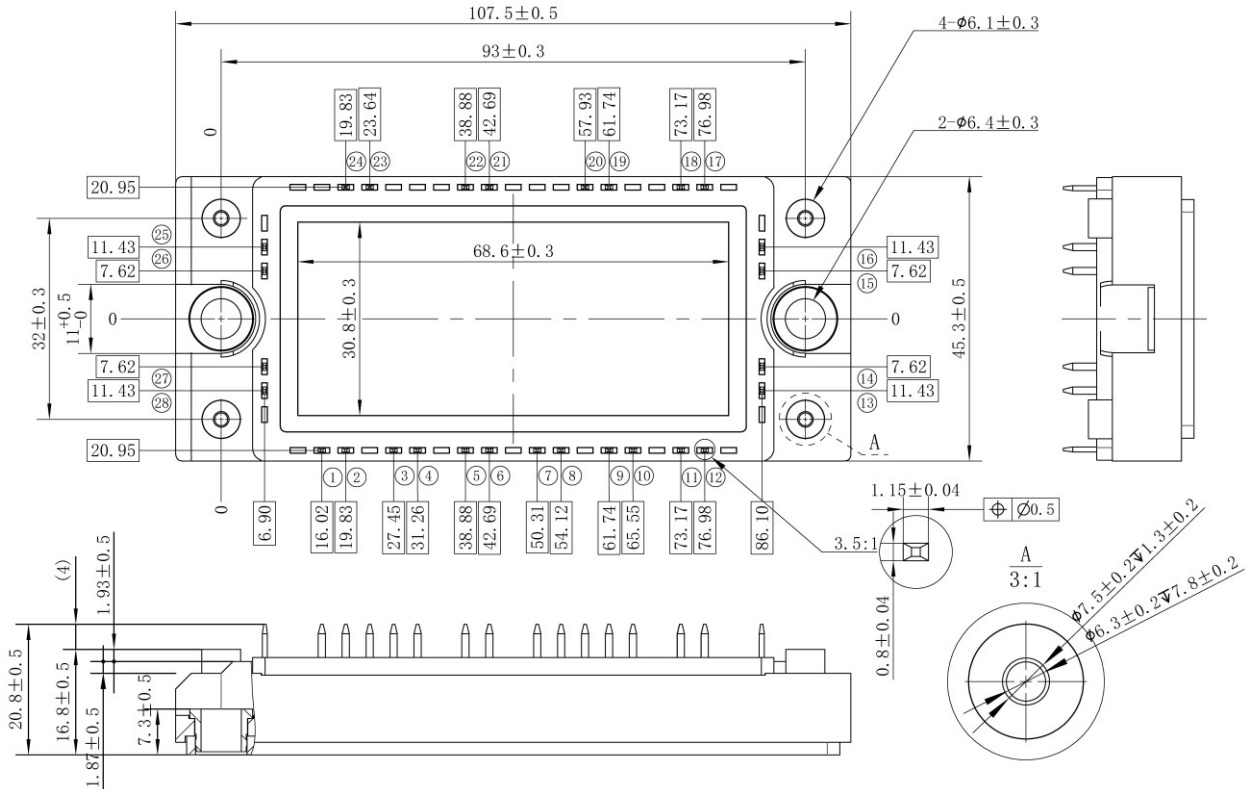


Figure 2. Pin configuration

### Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, $f = 50\text{Hz}$ , $t = 1\text{min}$	2.5	KV
CTI	-	>200	-
Module lead resistance, terminals – chip	$T_c = 25^\circ\text{C}$	0.8	m $\Omega$
Mounting torque for module mounting	M5	3 to 6	Nm
Weight	-	175	g

### Maximum Ratings (IGBT, Freewheeling Diode ,T<sub>j</sub>=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CES</sub>	Collector-Emitter Voltage	G-E Short	1200	V
V <sub>GES</sub>	Gate-Emitter Voltage	C-E Short	±20V	V
I <sub>C</sub>	DC Continuous Collector Current	T <sub>C</sub> =100°C	75	A
I <sub>CM</sub>	Pulse Collector Current	t <sub>p</sub> =1ms, Note1	150	A
P <sub>C</sub>	Maximum Power Dissipation	T <sub>C</sub> =25°C, T <sub>j</sub> =175°C(IGBT)	455	W
I <sub>F</sub>	Diode forward Current	-	75	A
I <sub>FRM</sub>	Repetitive peak forward Current	t <sub>p</sub> =1ms, Note1	150	A
t <sub>sc</sub>	Short Circuit Withstand Time	V <sub>GE</sub> =15V, V <sub>CE</sub> =600V, T <sub>j</sub> =150°C	10	us
T <sub>jmax</sub>	Max junction temperature	-	175	°C
T <sub>jop</sub>	Operating junction temperature	-	-40 to 150	°C
T <sub>stg</sub>	Storage temperature	-	-40 to 125	°C

Note1: Pulse width limited by maximum junction temperature

### NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R <sub>25</sub>	Resistance	T <sub>C</sub> =25°C	-	5	-	kΩ
ΔR/R	Deviation of R100	T <sub>C</sub> =100°C, R <sub>100</sub> =493Ω	-5	-	5	%
P <sub>25</sub>	Power dissipation	T <sub>C</sub> =25°C	-	-	20	mW
B <sub>25/50</sub>	B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15 K))]$	-	3375	-	K
B <sub>25/80</sub>	B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15 K))]$	-	3411	-	K
B <sub>25/100</sub>	B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15 K))]$	-	3433	-	K

### IGBT Electrical characteristics (T<sub>j</sub>=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit	
				Min.	Typ.	Max.		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =75A V <sub>GE</sub> =15V	T <sub>j</sub> =25°C	-	1.60	-	V	
			T <sub>j</sub> =125°C	-	1.78	-	V	
			T <sub>j</sub> =150°C	-	1.88	-	V	
V <sub>GE(th)</sub>	Gate-Emitter threshold Voltage	I <sub>C</sub> =2.8mA, V <sub>CE</sub> =V <sub>GE</sub>		5.0	5.8	6.5	V	
Q <sub>G</sub>	Gate charge	V <sub>GE</sub> = -15V to +15V		-	480	-	nC	
R <sub>Gint</sub>	Internal gate resistor	f=1M	T <sub>j</sub> =25°C	-	0	-	Ω	
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V f=1MHz	T <sub>j</sub> =25°C	-	5.20	-	nF	
C <sub>oes</sub>	Output Capacitance			-	0.66	-	nF	
C <sub>res</sub>	Reverse transfer Capacitance			-	0.42	-	nF	
I <sub>CEs</sub>	Collector- Emitter Cut off Current	V <sub>CE</sub> =1200V, V <sub>GE</sub> =0V		T <sub>j</sub> =25°C	-	-	1	mA
I <sub>GES</sub>	Gate-Emitter Leakage Current	V <sub>GE</sub> =20V, V <sub>CE</sub> =0V		T <sub>j</sub> =25°C	-	-	200	nA
t <sub>d(on)</sub>	Turn-on delay time	V <sub>CC</sub> =600V I <sub>C</sub> =75A V <sub>GE</sub> =+15V/-8V R <sub>Gon</sub> =R <sub>Goff</sub> =15Ω Inductive load	T <sub>j</sub> =25°C	-	102	-	ns	
			T <sub>j</sub> =150°C	-	110	-		
t <sub>r</sub>	Rise time		T <sub>j</sub> =25°C	-	44	-	ns	
			T <sub>j</sub> =150°C	-	41	-		
t <sub>d(off)</sub>	Turn-off delay time		T <sub>j</sub> =25°C	-	582	-	ns	
			T <sub>j</sub> =150°C	-	671	-		
t <sub>f</sub>	Fall time		T <sub>j</sub> =25°C	-	248	-	ns	
			T <sub>j</sub> =150°C	-	435	-		
E <sub>on</sub>	Turn-on power dissipation		T <sub>j</sub> =25°C	-	3.9	-	mJ	
			T <sub>j</sub> =150°C	-	6.8	-		
E <sub>off</sub>	Turn-off power dissipation		T <sub>j</sub> =25°C	-	6.2	-	mJ	
			T <sub>j</sub> =150°C	-	9.8	-		
R <sub>th(j-c)</sub>	Thermal Resistance, Junction to Case (IGBT)			-	0.33	-	°C /W	
R <sub>th(c-s)</sub>	Thermal Resistance, Case to sink (Conductive Grease applied) , Note1			-	0.15	-	°C /W	

Note1: Assumes Thermal Conductivity of grease is 2.8 W/m · K and thickness is 50um.

### Freewheeling Diode Electrical characteristics ( $T_j=25^\circ\text{C}$ unless otherwise specified, chip)

Symbol	Item	Condition	Value			Unit	
			Min.	Typ.	Max.		
$V_F$	Diode Forward Voltage	$I_F=75\text{A}, V_{GE}=0\text{V}$	$T_j=25^\circ\text{C}$	-	1.80	-	V
			$T_j=125^\circ\text{C}$	-	1.55	-	
			$T_j=150^\circ\text{C}$	-	1.50	-	
$t_{rr}$	Diode Reverse Recovery Time	(Switch side) $V_{CC}=600\text{V}, I_C=75\text{A}$	$T_j=25^\circ\text{C}$		436		ns
			$T_j=150^\circ\text{C}$		662		
$I_{RM}$	Peak reverse recovery Current	$V_{GE}=+15\text{V}/-8\text{V}$ $R_{Gon} = R_{Goff}=15\Omega$	$T_j=25^\circ\text{C}$	-	33	-	A
			$T_j=150^\circ\text{C}$	-	47	-	
$Q_{rr}$	Recovered charge	(FRD side) $V_{rr}=600\text{V}, I_r=75\text{A}$	$T_j=25^\circ\text{C}$	-	14.9	-	uC
			$T_j=150^\circ\text{C}$	-	30.1	-	
$E_{rr}$	Reverse recovered energy	$V_{GE}=+15\text{V}/-8\text{V}$ Inductive load switching operation	$T_j=25^\circ\text{C}$	-	2.7	-	mJ
			$T_j=150^\circ\text{C}$	-	6.4	-	
$R_{th(j-c)}$	Thermal Resistance, Junction to Case (Diode)		-	0.44	-	$^\circ\text{C}/\text{W}$	
$R_{th(c-s)}$	Thermal Resistance, Case to sink (Conductive Grease applied), Note1		-	0.20	-	$^\circ\text{C}/\text{W}$	

Note1: Assumes Thermal Conductivity of grease is  $2.8 \text{ W/m} \cdot \text{K}$  and thickness is  $50\mu\text{m}$ .

### Test Conditions

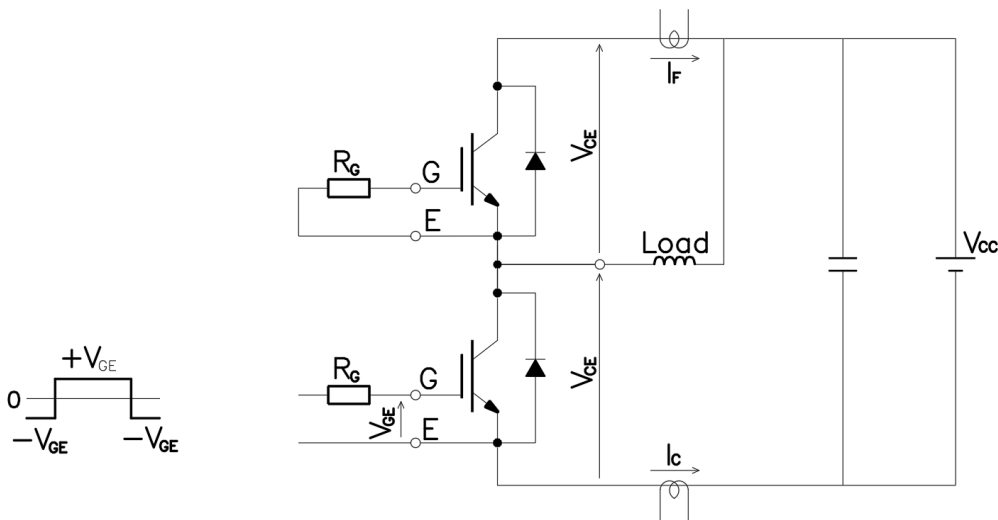


Figure 3. Switching time measure circuit

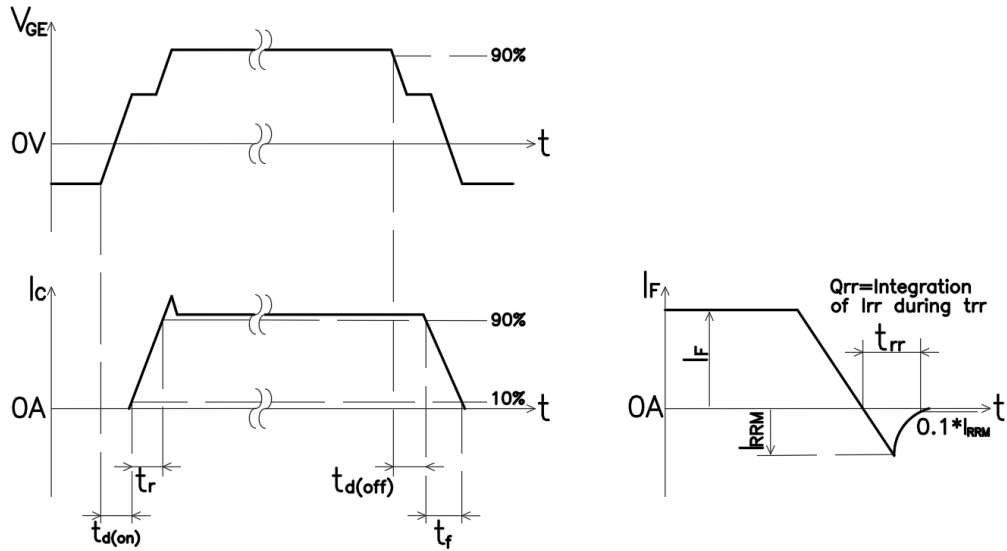


Figure 4. Switching time definition

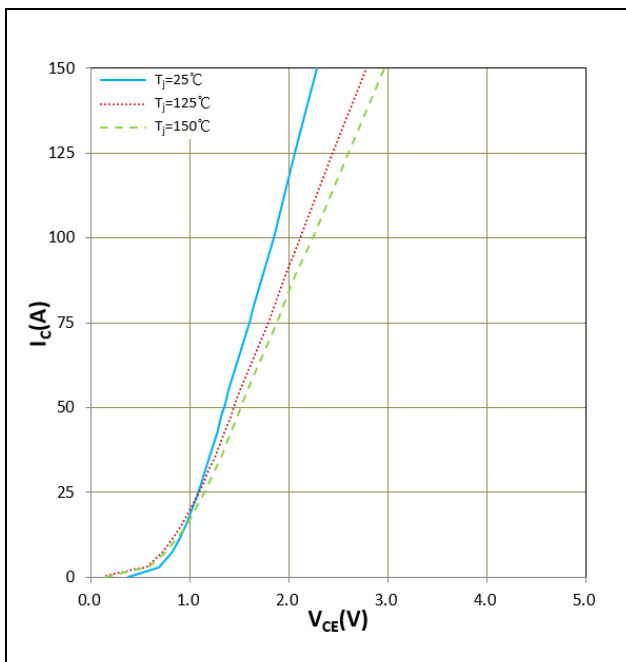


Figure 5.  $I_c$  vs  $V_{CE}$   
 $V_{GE} = 15V$

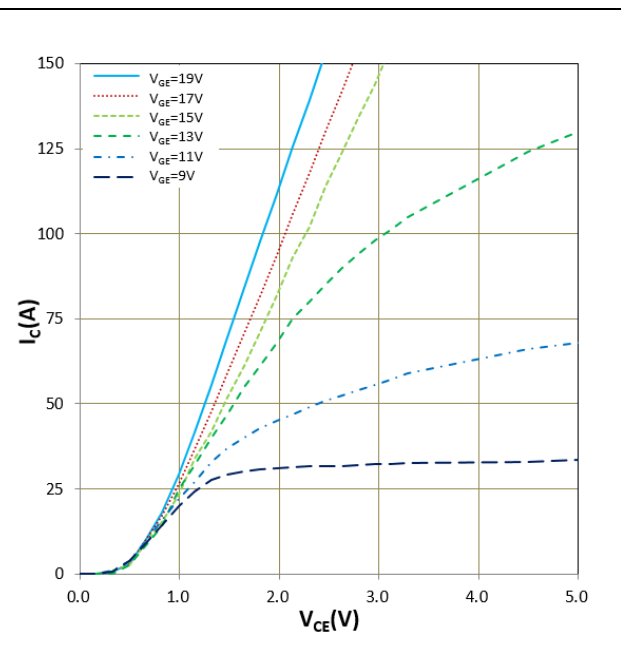


Figure 6.  $I_c$  vs  $V_{CE}$   
 $T_j = 150^\circ C$

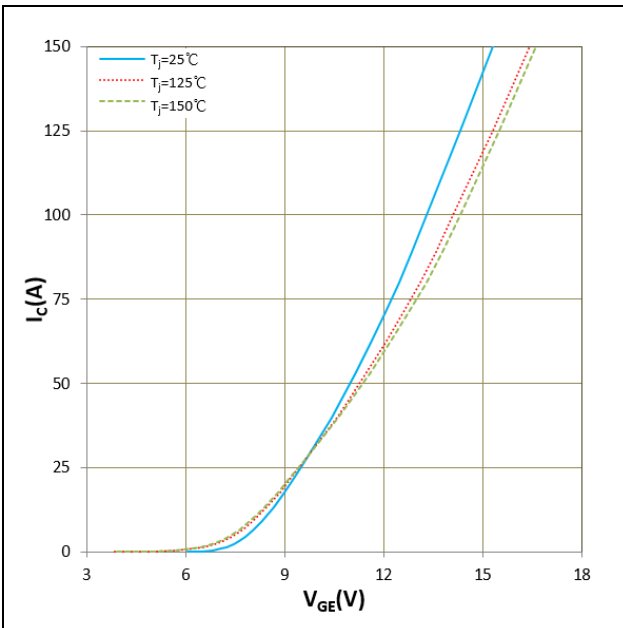


Figure 7.  $I_c$  vs  $V_{GE}$   
 $V_{CE} = 20V$

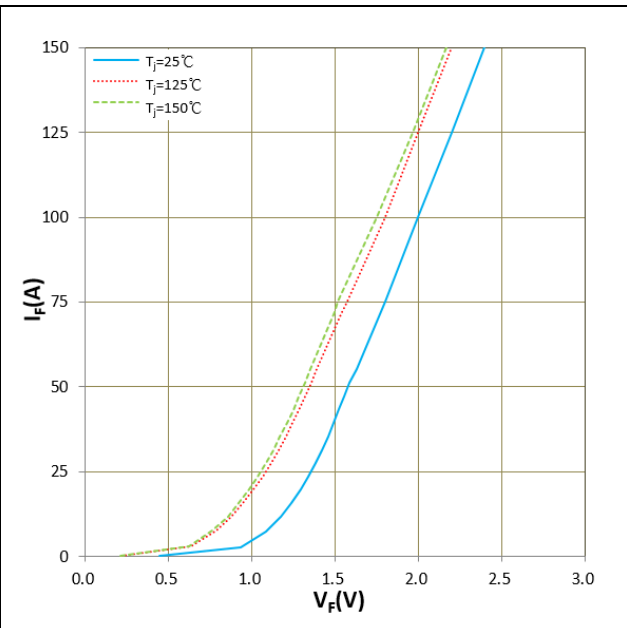


Figure 8.  $I_F$  vs  $V_F$

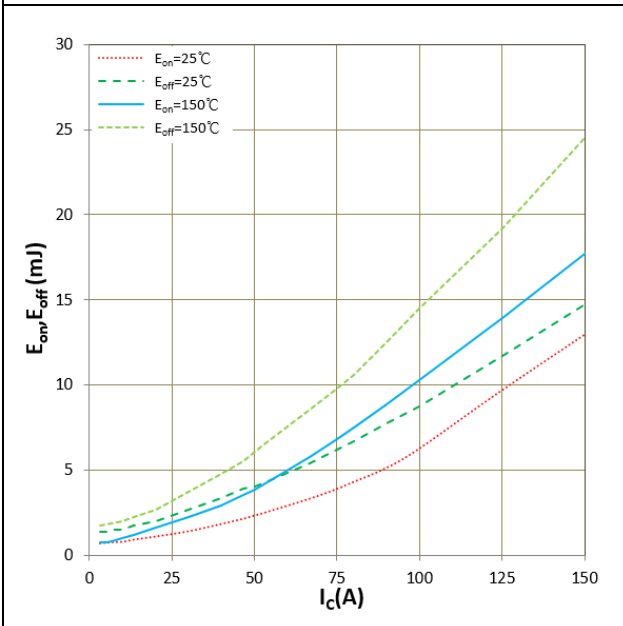


Figure 9.  $E_{on}$ ,  $E_{off}$  vs  $I_c$ (Typ)  
 $V_{CC} = 600V$ ,  $V_{GE} = +15V/-8V$ ,  $R_{Gon} = R_{Goff} = 15\Omega$   
Inductive Load

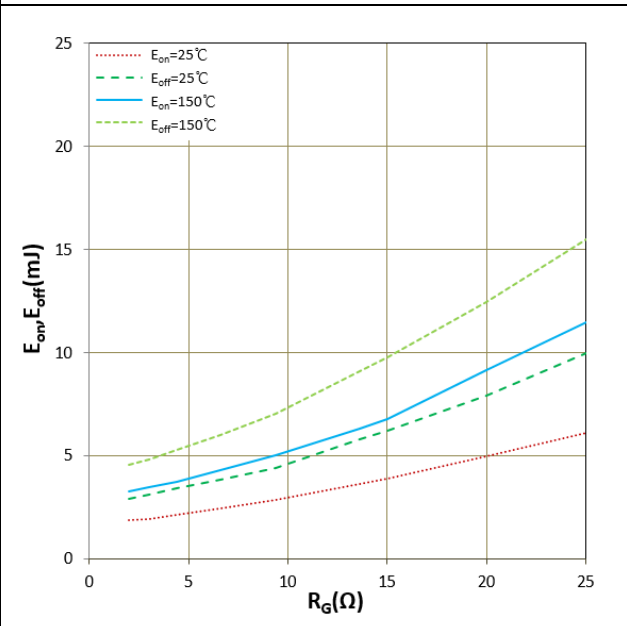
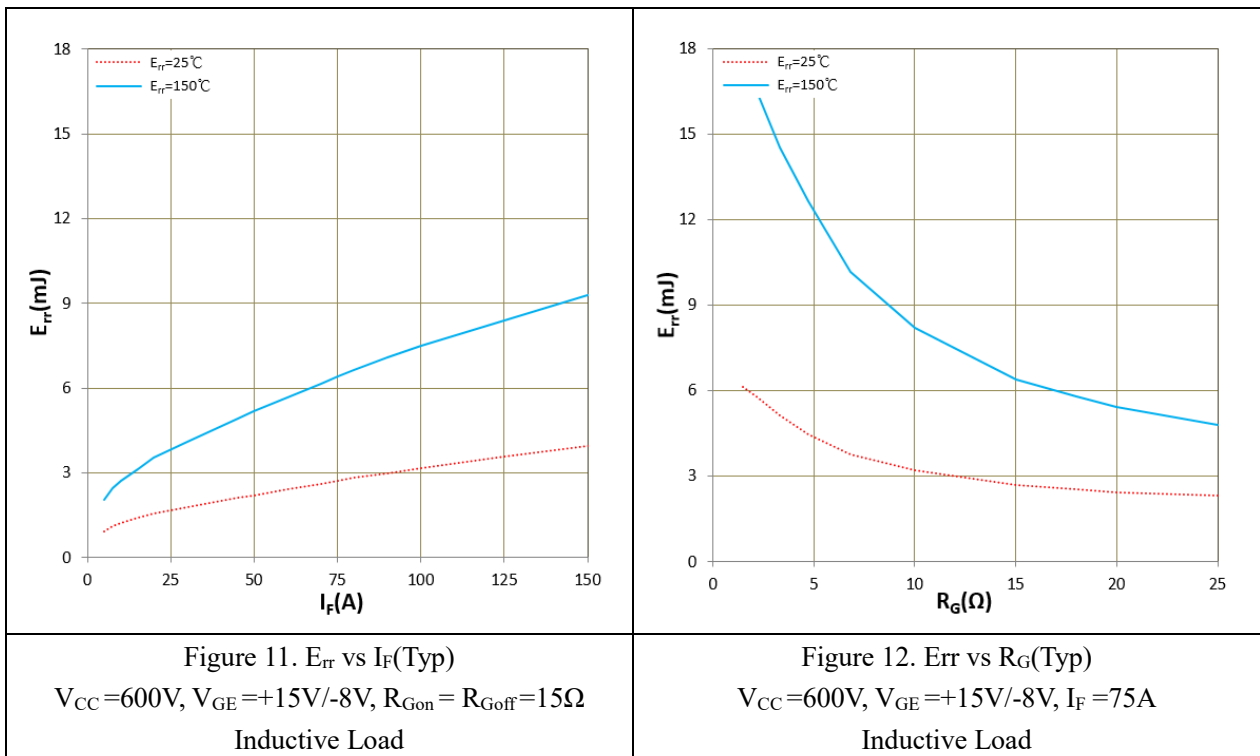


Figure 10.  $E_{on}$ ,  $E_{off}$  vs  $R_G$ (Typ)  
 $V_{CC} = 600V$ ,  $V_{GE} = +15V/-8V$ ,  $I_c = 75A$   
Inductive Load



### IMPORTANT NOTICE:

This product data sheet describes the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively under the terms and conditions of the supply agreement. There will be no guarantee or of any kind for the product and its characteristics.

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